

10/019540

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- 1 -

Docket: 740819-724

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re New National Phase Patent Application of )  
Takashi NISHIKAWA )  
International Application No. PCT/JP00/04477 ) Attn: Applications  
International Filing Date: July 6, 2000 ) Branch  
For: LAYERED STRUCTURE, METHOD FOR )  
MANUFACTURING THE SAME, AND )  
SEMICONDUCTOR ELEMENT ) Date: January 3, 2002

7/a  
D. Scott  
8-7-02

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents and Trademarks  
Washington, D.C. 20231

Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIMS:

Please amend claims 10 and 13 as follows: Please note that the claims are presented below in their amended form. They are further presented as an Attachment to the Amendment whereby the amendments to the claims are outlined using the conventional method of bracketing and underlining.

a<sup>1</sup>  
10. (Amended) The method for manufacturing a layered structure according to claim 9, wherein the nitrogen gas is turned into a plasma using a plasma cell.

a<sup>2</sup>  
13. (Amended) The method for manufacturing a layered structure according to claim 11 or claim 12, wherein a step (b) at least one of oxygen, hydrogen and sulfur is added to the AlN film to relieve strain in the AlN layer resulting from lattice mismatch with the Si crystal layer.